

# IHP 0.13 $\mu$ & 0.25 $\mu$ SiGe:C BiCMOS MPW & SMALL VOLUME

EUROPRACTICE IC Service offers Multi-Project-Wafer (MPW) services and small volume production in high frequency SiGe:C BiCMOS from IHP in Europe.

## Features and Benefits

- Small minimum area pricing for academic customers
- Regularly scheduled MPW runs
- CADENCE mixed signal design kits and Agilent ADS support
- 5 to 7 metal layers, bumping for all technologies
- High performance BiCMOS technology with integrated Silicon Photonic devices
- RFMEMS Switch



SG13G2	High performance BiCMOS 0.13 $\mu$ m with SiGe:C npn-HBTs up to $f_T / f_{max} = 300/500$ GHz, 3.3V I/O CMOS and 1.2V logic CMOS
SG13S	High performance BiCMOS 0.13 $\mu$ m with SiGe:C npn-HBTs up to $f_T / f_{max} = 250/300$ GHz, 3.3V I/O CMOS and 1.2V logic CMOS
SG25H3	High performance BiCMOS 0.25 $\mu$ m SiGe:C technology with a set of npn-HBTs ranging from a higher RF performance ( $f_T/f_{max} = 110$ GHz/180 GHz) to higher breakdown voltages up to 7 V
SG25H5_EPIC	high performance BiCMOS technology with integrated Silicon Photonic devices. It combines SG25H5 BiCMOS process with RF performance ( $f_T/f_{max} = 250$ GHz/300 GHz) and photonic devices
SGB25V	Cost effective SiGe:C technology with npn-HBTs up to 7V breakdown voltage. HBT devices with up to $f_T / f_{max} = 75/95$ GHz

Devices	Performance	Technologies			
		SG13G2/S	SG25H5_EPIC	SG25H3	SGB25V
HBT	$f_T/f_{max}/BV_{CE0}$ (GHz/GHz/V)	300 / 500 / 1.6 250 / 300 / 1.7 45 / 120 / 3.7	250 / 300 / 1.9	120 / 140 / 2.4 110 / 180 / 2.3 45 / 140 / 5 30 / 80 / 7	75 / 95 / 2.4 45 / 90 / 4 25 / 70 / 7